



SamHop Microelectronics Corp.



# STM4472

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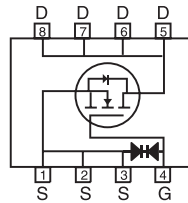
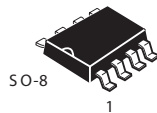
## N-Channel Enhancement Mode Field Effect Transistor

### PRODUCT SUMMARY

V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> ( mΩ ) Max
40V	7 A	24 @ V <sub>GS</sub> = 10V 30 @ V <sub>GS</sub> = 4.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous <sup>a</sup> @ T <sub>a</sub>	I <sub>D</sub>	7	A
		5.9	A
-Pulsed <sup>b</sup>	I <sub>DM</sub>	28	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	1.7	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	3	W
		2.1	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	40	°C/W
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# STM4472

N-Channel ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V			1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±10	uA
ON CHARACTERISTICS <sup>b</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250uA	1	1.8	3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A		18	24	m ohm
		V <sub>GS</sub> =4.5V, I <sub>D</sub> = 5A		23	30	m ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 10V	15			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 7A		12.5		S
DYNAMIC CHARACTERISTICS <sup>c</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =20 V, V <sub>GS</sub> = 0V f =1.0MHz		700		pF
Output Capacitance	C <sub>OSS</sub>			140		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			80		pF
SWITCHING CHARACTERISTICS <sup>c</sup>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 20V I <sub>D</sub> = 1 A V <sub>GS</sub> = 10V R <sub>GEN</sub> = 3.3 ohm		13.4		ns
Rise Time	t <sub>r</sub>			12.5		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			43.3		ns
Fall Time	t <sub>f</sub>			8.5		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =7A,V <sub>GS</sub> =10V		13.5		nC
		V <sub>DS</sub> =20V, I <sub>D</sub> =7A,V <sub>GS</sub> =4.5V		6.7		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> = 7 A V <sub>GS</sub> =4.5V		1.8		nC
Gate-Drain Charge	Q <sub>gd</sub>			2.4		nC

# STM4472

## ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS <sup>b</sup>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{V}, I_S = 1.7\text{A}$		0.78	1.2	V

### Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.

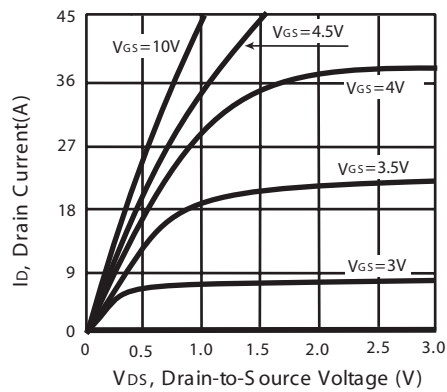


Figure 1. Output Characteristics

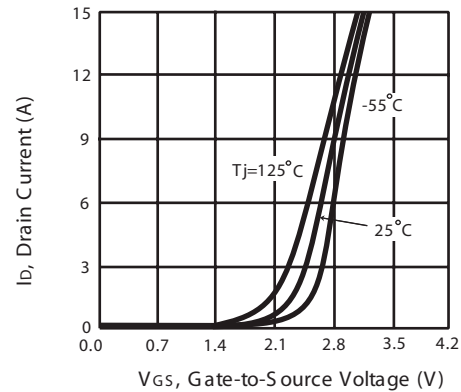


Figure 2. Transfer Characteristics

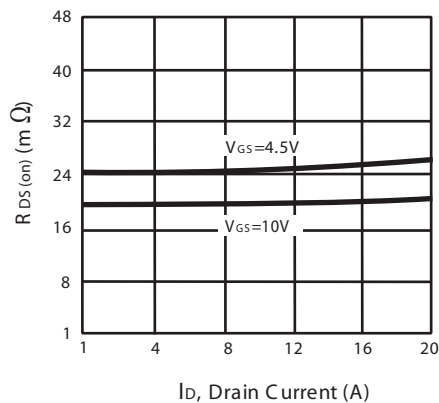


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

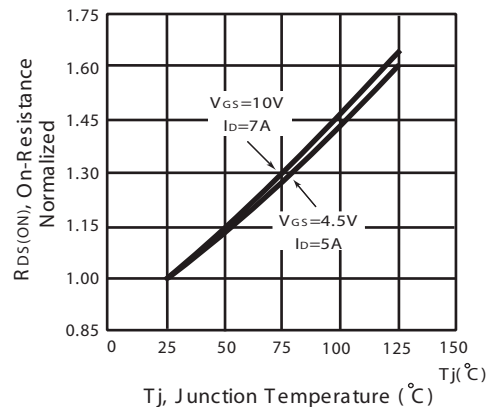


Figure 4. On-Resistance Variation with Drain Current and Temperature

# STM4472

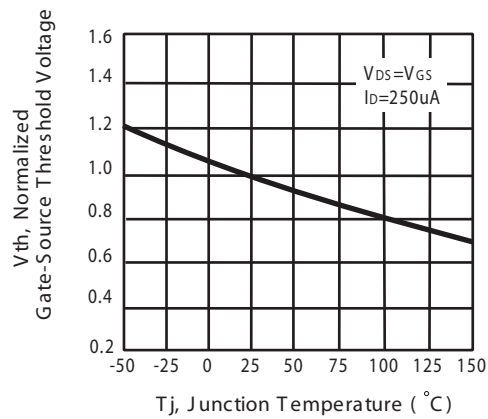


Figure 5. Gate Threshold Variation with Temperature

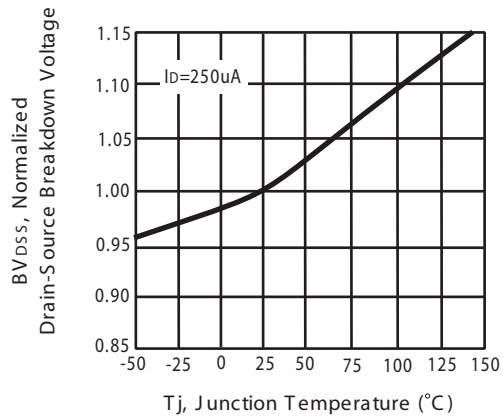


Figure 6. Breakdown Voltage Variation with Temperature

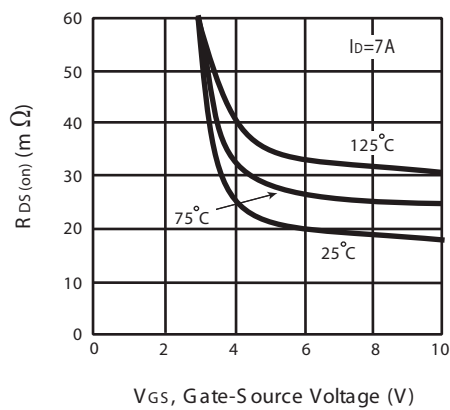


Figure 7. On-Resistance vs. Gate-Source Voltage

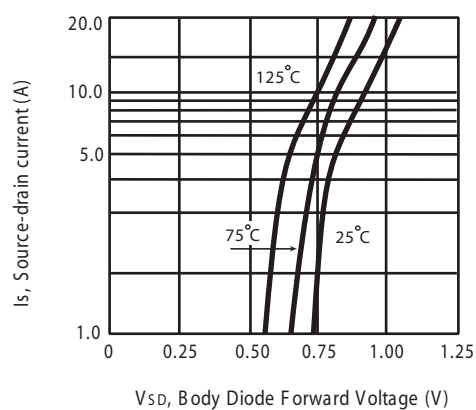
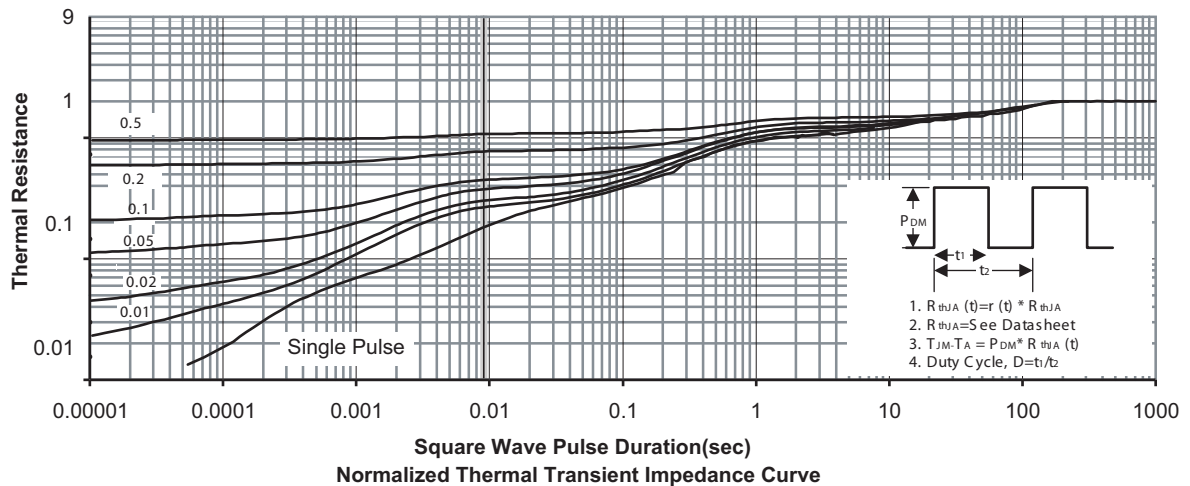
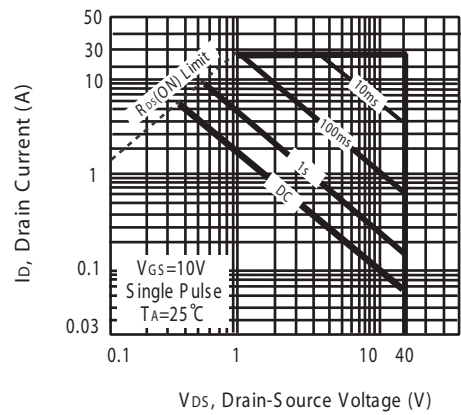
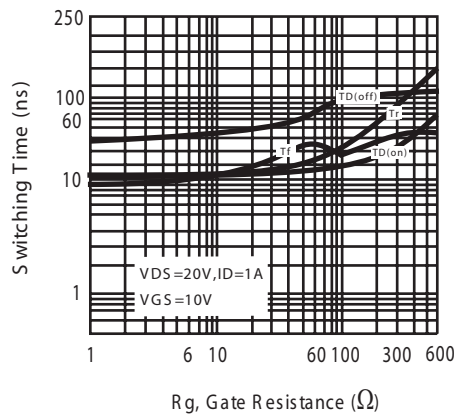
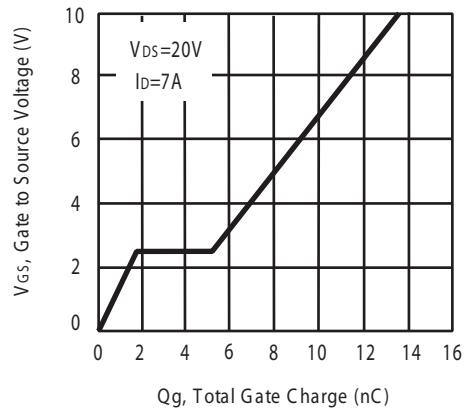
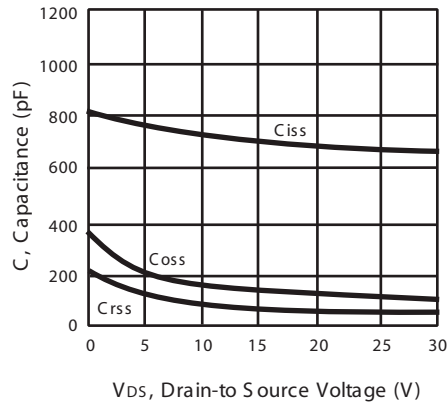


Figure 8. Body Diode Forward Voltage Variation with Source Current

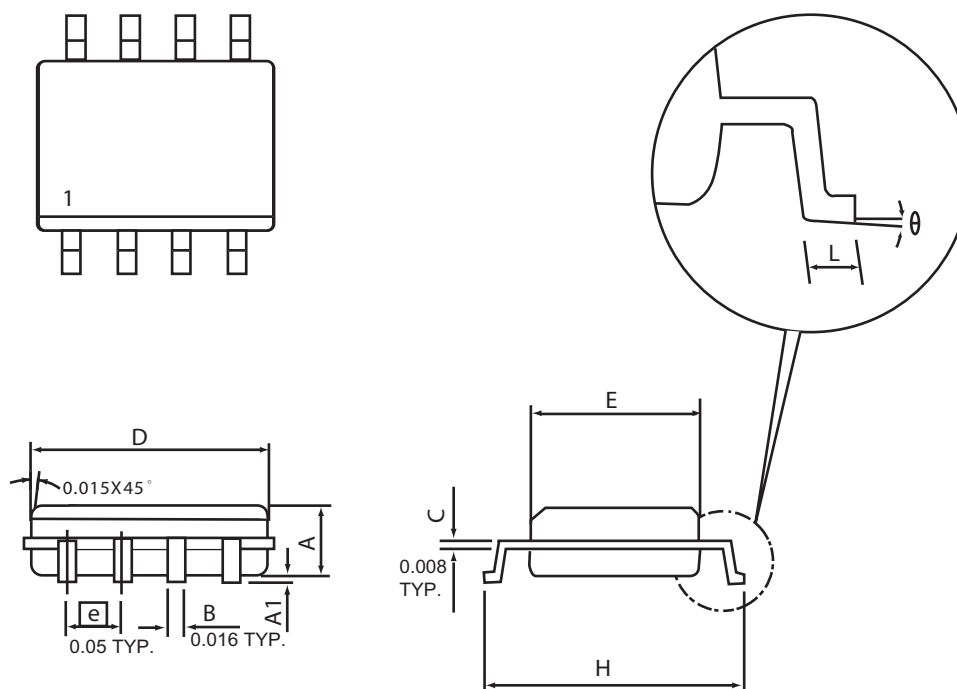
# STM4472



# STM4472

## PACKAGE OUTLINE DIMENSIONS

### SO-8

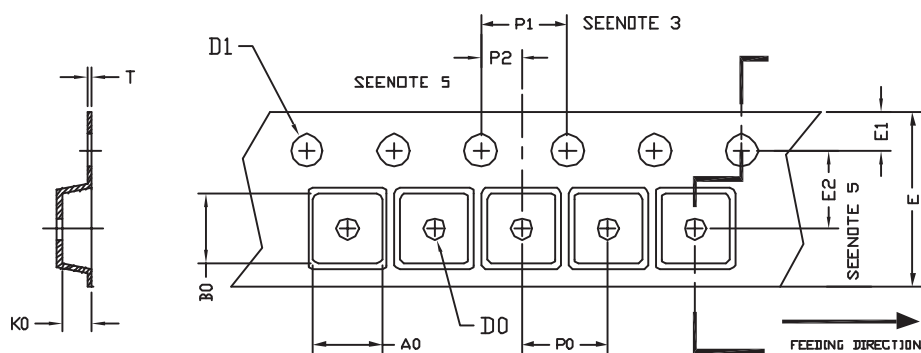


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
$\theta$	0°	8°	0°	8°

# STM4472

## SO-8 Tape and Reel Data

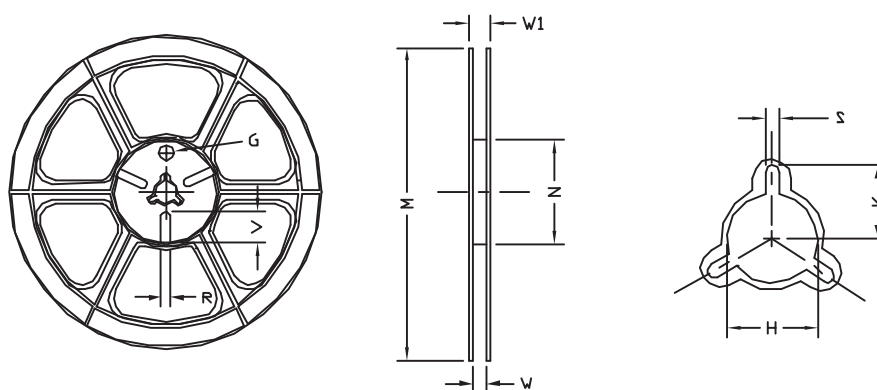
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 $\pm 0.3$	1.75	5.5 $\pm 0.05$	8.0	4.0	2.0 $\pm 0.05$	0.3 $\pm 0.05$

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 $\pm 1$	62 $\pm 1.5$	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 $\pm 0.15$	---	---	---